

STPS40M80C

Power Schottky rectifier

Features

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified

Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK and D²PAK, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 20 A
V _{RRM}	80 V
T _j (max)	175 °C
V _F (typ)	475 mV

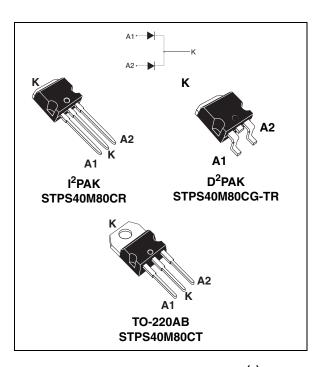
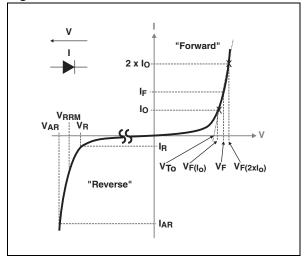


Figure 1. Electrical characteristics^(a)



V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 11*. V_{AR} and I_{AR} are pulse measurements (t_p < 1 μs). V_R, I_R, V_{RRM} and V_F, are static characteristics

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1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at $T_{amb} = 25$ °C unless otherwise specified)

Symbol	Parameter				Value	Unit
V _{RRM}	Repetitive peak reverse vol	tage			80	V
I _{F(RMS)}	Forward rms current				30	Α
I _{F(AV)}	Average forward current, δ	$T_c = 150 ^{\circ}\text{C}$ Per diode $T_c = 150 ^{\circ}\text{C}$ Per device			20 40	Α
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}$ $T_c = 25 ^{\circ}\text{C}$			200	Α
P _{ARM} ⁽¹⁾	Repetitive peak avalanche	power	$T_j = 25 ^{\circ}\text{C}, t_p$	= 1 µs	10000	W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	$t_p < 1 \mu s, T_j < 150 °C, I_{AR} < 30 A$			100	V
V _{ASM} ⁽²⁾	Maximum single pulse peak avalanche voltage	t _p < 1 μs, T _j < 150 °C, I _{AR} < 30 A			100	V
T _{stg}	Storage temperature range			-65 to +175	°C	
Tj	Maximum operating junction temperature ⁽³⁾			175	°C	

For temperature or pulse time duration deratings, please refer to figure 3 and 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

Table 3. Thermal parameters

Symbol	Parameter		Value	Unit
В	Junction to case	oer diode	1.30	°C/W
R _{th(j-c)}		total	0.75	C/VV
R _{th(c)}	Coupling		0.20	°C/W

When the two diodes 1 and 2 are used simultaneously:

$$\Delta T_i(diode 1) = P(diode 1) \times R_{th(i-c)}(Per diode) + P(diode 2) \times R_{th(c)}$$

^{2.} See Figure 11

^{3.} $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

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Table 4.	Static electrical	characteristics ((per diode)
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Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V - V	-	15	65	μΑ
'R`	neverse leakage current	T _i = 125 °C	$V_R = V_{RRM}$	-	15	40	mA
	T _j = 25 °C	-	0.550	0.600			
		T _j = 125 °C	I _F = 10 A	-	0.475	0.510	
V _E ⁽²⁾	V (2)	T _j = 25 °C	I _F = 20 A	-	0.655	0.735	V
VF` ′	Forward voltage drop	T _j = 125 °C	1 IF = 20 A	-	0.570	0.635	V
		T _j = 25 °C	L = 40 A	-	0.800	0.920	
		T _j = 125 °C	I _F = 40 A	-	0.680	0.795	

- 1. Pulse test: t_p = 5 ms, δ < 2 %
- 2. Pulse test: t_p = 380 μ s, δ < 2 %

To evaluate the conduction losses use the following equation:

 $P = 0.475 \times I_{F(AV)} + 0.008 \times I_{F}^{2}_{(RMS)}$

Figure 2. Average forward power dissipation Figure 3. versus average forward current (per diode)

Average forward current versus ambient temperature (δ = 0.5, per diode)

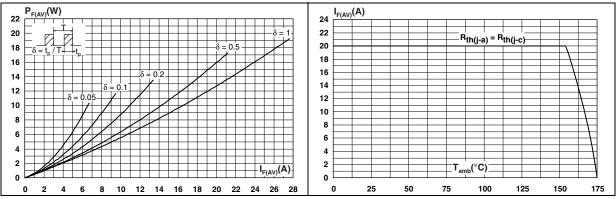
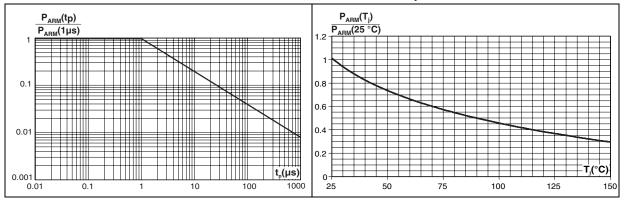


Figure 4. Normalized avalanche power derating versus pulse duration

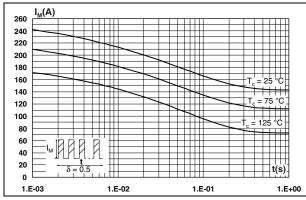
Figure 5. Normalized avalanche power derating versus junction temperature



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Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 7. Relative thermal impedance junction to case versus pulse duration



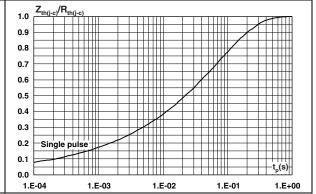
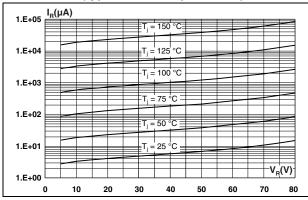


Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)



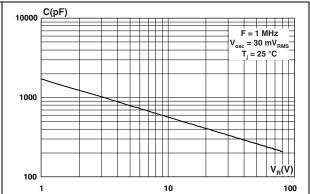


Figure 10. Forward voltage drop versus forward current (per diode)

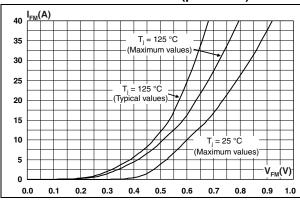
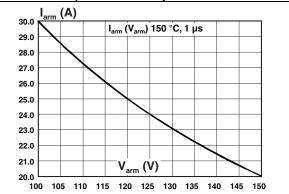


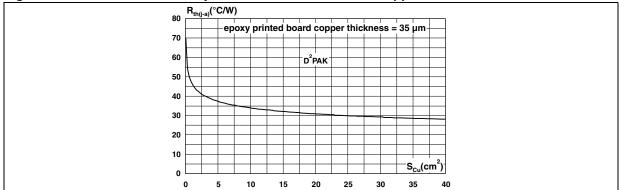
Figure 11. Reverse safe operating area $(t_p < 1 \mu s \text{ and } T_i < 150 \,^{\circ}\text{C})$



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Figure 12. Thermal resistance junction to ambient versus copper surface under tab for ${\rm D^2PAK}$

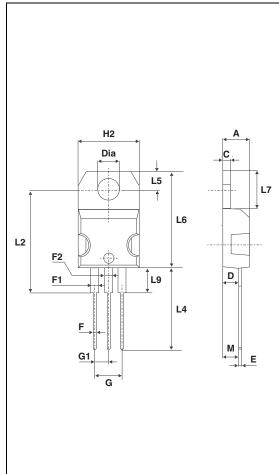


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 5. TO-220AB dimensions



	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
Е	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
F2	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
G1	2.40	2.70	0.094	0.106	
H2	10	10.40	0.393	0.409	
L2	16.4	Тур.	0.645 Typ.		
L4	13	14	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6	Тур.	0.102	2 Тур.	
Dia.	3.75	3.85	0.147	0.151	

Table 6. D²PAK dimensions

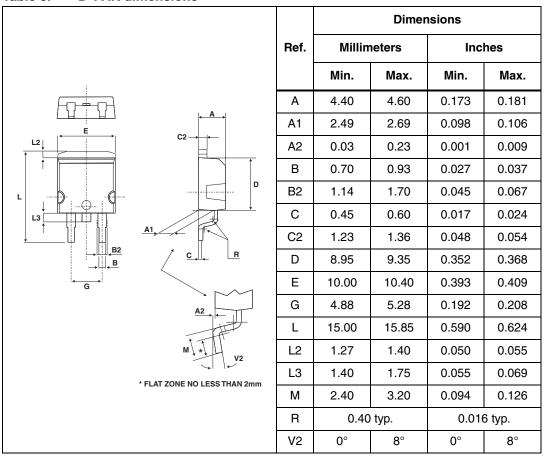
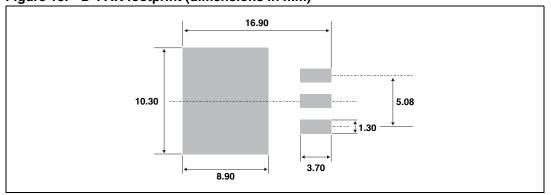
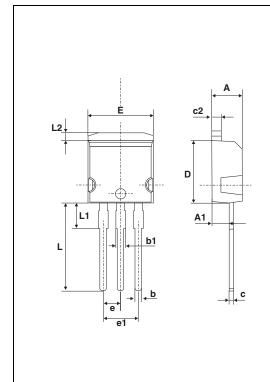


Figure 13. D²PAK footprint (dimensions in mm)



Package information STPS40M80C

Table 7. I²PAK dimensions



	Dimensions			
Ref.	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
С	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
е	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
Е	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS40M80CT	STPS40M80CT	TO-220AB	1.9 g	50	Tube
STPS40M80CR	STPS40M80CR	I ² PAK	1.49 g	50	Tube
STPS40M80CG-TR	STPS40M80CG	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 9. Revision history

Date	Revision	Changes
11-Apr-2011	1	First issue.

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